HIGH VOLTAGE SILICON RECTIFIERS
Reverse Voltage - 1200 to 2000 Volts
Forward Current - 0.2 to 0.5 Ampere


Dimensions in mm

## Absolute Maximum Ratings and Characteristics

Ratings at $25^{\circ} \mathrm{C}$ ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz . resistive or inductive load. For capacitive load, derate current by $20 \%$.

|  |  | Symbols | R1200 | R1500 | R1800 | R2000 | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Maximum recurrent peak reverse voltage |  | $\mathrm{V}_{\text {RRM }}$ | 1200 | 1500 | 1800 | 2000 | Volts |
| Maximum RMS voltage |  | $\mathrm{V}_{\text {RMS }}$ | 840 | 1050 | 1260 | 1400 | Volts |
| Maximum DC blocking voltage |  | $V_{D C}$ | 1200 | 1500 | 1800 | 2000 | Volts |
| Maximum average forward rectified current at $\mathrm{T}_{\mathrm{A}}=55^{\circ} \mathrm{C}$ |  | Io |  | 500 |  | 200 | mAmps |
| Peak forward surge current, $\quad 8.3 \mathrm{~ms}$ single half sine-wave superimposed on rated load(JEDEC method) |  | $\mathrm{I}_{\text {FSM }}$ |  |  |  |  | Amps |
| Maximum instantaneous forward voltage at 0.5A/0.2A DC |  | $V_{F}$ |  | 2 |  | 3 | Volts |
| Maximum DC reverse current at rated DC blocking voltage | $@ T_{\text {A }}=25^{\circ} \mathrm{C}$ | $I_{R}$ |  |  |  |  |  |
|  | $@ \mathrm{~T}_{\mathrm{A}}=100^{\circ} \mathrm{C}$ |  |  |  |  |  |  |
| Maximum full load reverse current average, Full cycle $0.375^{\prime \prime}(9.5 \mathrm{~mm})$ lead length at $\mathrm{T}_{\mathrm{L}}=75^{\circ} \mathrm{C}$ |  |  |  |  |  |  | $\mu \mathrm{Amps}$ |
| Typical junction capacitance (Note) |  | C |  |  |  |  | pF |
| Operating and storage temperature range |  | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\mathrm{s}}$ |  | -55 to | +150 |  | ${ }^{\circ} \mathrm{C}$ |

Notes: Measured at $1 \mathrm{MH}_{z}$ and applied reverse voltage of 4 volts.

FIG. 1 - TYPICAL FORWARD CURRENT


FIG. 2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT



ISO 9001 REGISTERED

